

Title (en)
METHOD FOR PRODUCING SEMICONDUCTOR CHIPS

Title (de)
VERFAHREN ZUR HERSTELLUNG VON HALBLEITERCHIPS

Title (fr)
PROCÉDÉ POUR PRODUIRE DES PUCES SEMI-CONDUCTRICES

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Application
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Abstract (en)
[origin: WO2009079982A2] The invention relates to method for producing a plurality of semiconductor chips (1). A plurality of semiconductor elements (2) is made available on a substrate (8), the semiconductor elements (2) being interspaced by gaps (25). A structured carrier (33) is made available and comprises a plurality of elevations (35). The structured carrier (33) is positioned relative to the substrate (8) in such a manner that the elevations of the structured carrier (33) extend into the gaps (25) between the semiconductor elements (2), thereby producing a mechanically stable composite (38) which comprises the substrate (8) and the structured carrier (33). The composite (38) is subdivided into a plurality of semiconductor chips (1). The invention further relates to a semiconductor chip.

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Citation (search report)
See references of WO 2009079982A2

Citation (examination)

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- EP 1690300 A2 20060816 - MATSUSHITA ELECTRIC IND CO LTD [JP]
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